

L Number	Hits	Search Text	DB	Time stamp
24	1	(impurity or dopant or diffusion) adj (region or layer or film) adj formed adj above adj substrate	USPAT; US-PGPUB	2003/03/20 18:38
26	72	(thin adj film adj transistor) and (electron adj emitter)	USPAT; US-PGPUB	2003/03/20 19:10
27	1	5985708.pn. and (si or ge or gap or inp or ingaas or ingap)	USPAT; US-PGPUB	2003/03/20 19:12
28	1	5985708.pn. and concentration	USPAT; US-PGPUB	2003/03/20 19:22
29	1	5985708.pn. and terminal	USPAT; US-PGPUB	2003/03/20 19:28
30	1	4325084.pn. and (si or ge or gap or inp or ingaas or ingap)	USPAT; US-PGPUB	2003/03/20 20:20
31	1	4325084.pn. and silicon	USPAT; US-PGPUB	2003/03/20 19:29
32	1	6242770.pn. and (wafer area)	USPAT; US-PGPUB	2003/03/20 20:50
33	0	6153014.pn. and uniform	USPAT; US-PGPUB	2003/03/20 21:07
35	383	(electron adj emitters) and 257/\$.ccls.	USPAT; US-PGPUB	2003/03/20 21:08